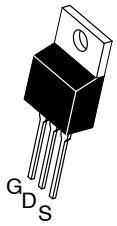
MOSFET – N-Channel, POWERTRENCH®

100 V, 50 A, 15 mΩ

FDP150N10A

V_{DSS}	$R_{DS(on)}$ MAX	I_D MAX
100 V	15.0 mΩ @ 10 V	50 A



TO−220
CASE 221A

Description

This N−Channel MOSFET is produced using **onsemi**'s advanced POWERTRENCH process that has been tailored to minimize the on−state resistance while maintaining superior switching performance.

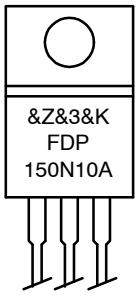
Features

- $R_{DS(on)}$ = 12.5 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 50 A
- Fast Switching Speed
- Low Gate Charge, Q_G = 16.2 nC (Typ.)
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

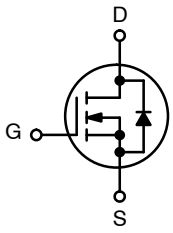
Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Motor Drives and Uninterruptible Power Supplies
- Micro Solar Inverter

MARKING DIAGRAM



&Z	= Assembly Plant Code
&3	= 3−Digit Date Code Format
&K	= 2−Digits Lot Run Traceability Code
FDP150N10A	= Device Code



N−Channel MOSFET

ORDERING INFORMATION

See detailed ordering and shipping information on page 8 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter		FDP150N10A_F102	Unit
V_{DSS}	Drain to Source Voltage		100	V
V_{GSS}	Gate to Source Voltage		±20	V
I_D	Drain Current	– Continuous (T_C = 25°C)	50	A
		– Continuous (T_C = 100°C)	36	
I_{DM}	Drain Current	– Pulsed (Note 1)	200	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		84.6	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns
P_D	Power Dissipation	(T_C = 25°C)	91	W
		– Derate Above 25°C	0.61	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		–55 to +175	°C
T_L	Maximum Lead Temperature for Soldering, 1/8” from Case for 5 Seconds		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse−width limited by maximum junction temperature.
2. L = 2 mH, I_{AS} = 9.2 A, R_G = 25 Ω, starting T_J = 25°C.
3. $I_{SD} \le$ 100 A, di/dt ≤ 200 A/μs, $V_{DD} \le BV_{DSS}$, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	FDP150N10A_F102	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.6	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	100	–	–	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	–	0.08	–	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80 V, V_{GS} = 0 V	–	–	1	μA
		V_{DS} = 80 V, T_C = 150°C	–	–	500	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	–	–	±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2.0	–	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 50 A	–	12.5	15.0	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 50 A	–	40	–	S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz	–	1080	1440	pF
C_{oss}	Output Capacitance		–	267	355	pF
C_{rss}	Reverse Transfer Capacitance		–	11	–	pF
$C_{oss(er)}$	Energy Related Output Capacitance	V_{DS} = 50 V, V_{GS} = 0 V	–	436	–	pF
$Q_{g(tot)}$	Total Gate Charge at 10 V	V_{DS} = 50 V, V_{GS} = 10 V, I_D = 50 A, (Note 4)	–	16.2	21.0	nC
Q_{gs}	Gate to Source Gate Charge		–	5.3	–	nC
Q_{gs2}	Gate Charge Threshold to Plateau		–	2.6	–	nC
Q_{gd}	Gate to Drain “Miller” Charge		–	3.7	–	nC
ESR	Equivalent Series Resistance (G–S)	f = 1 MHz	–	1.3	–	Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = 50 V, I_D = 50 A, V_{GS} = 10 V, R_G = 4.7 Ω (Note 4)	–	13	36	ns
t_r	Turn–On Rise Time		–	16	42	ns
$t_{d(off)}$	Turn–Off Delay Time		–	21	52	ns
t_f	Turn–Off Fall Time		–	5	20	ns
DRAIN–SOURCE DIODE CHARACTERISTICS						
I_S	Maximum Continuous Drain to Source Diode Forward Current		–	–	50	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		–	–	200	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 50 A	–	–	1.3	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, V_{DD} = 50 V, I_{SD} = 50 A, dI_F/dt = 100 A/μs	–	50	–	ns
Q_{rr}	Reverse Recovery Charge		–	55	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

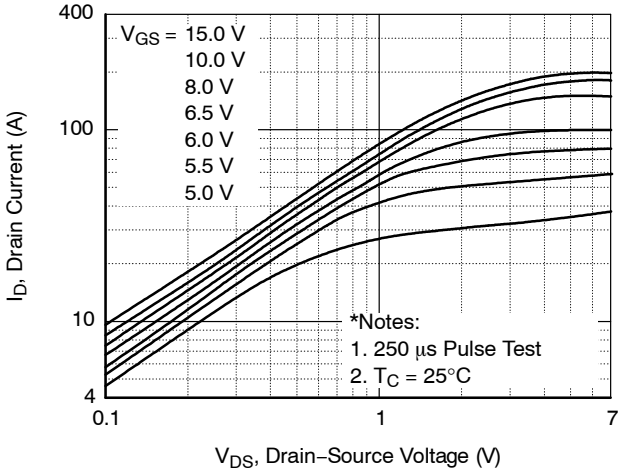


Figure 1. On−Region Characteristics

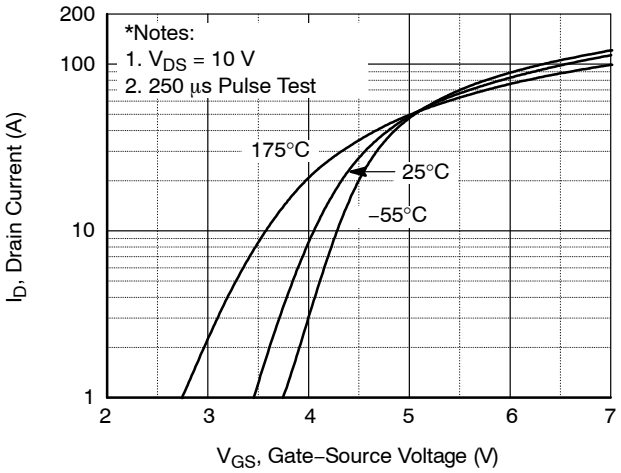


Figure 2. Transfer Characteristics

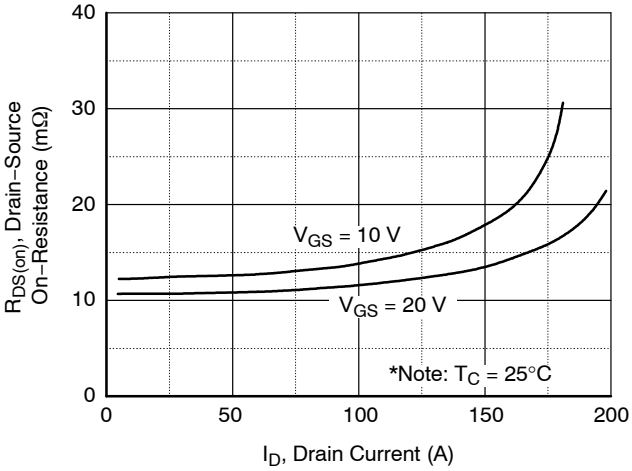


Figure 3. On−Resistance Variation vs. Drain Current and Gate Voltage

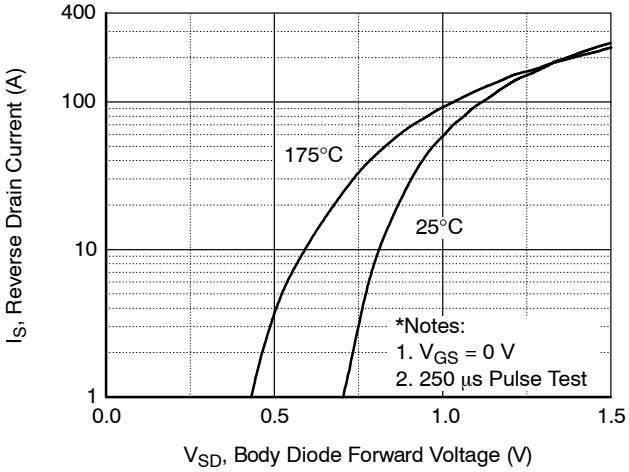


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

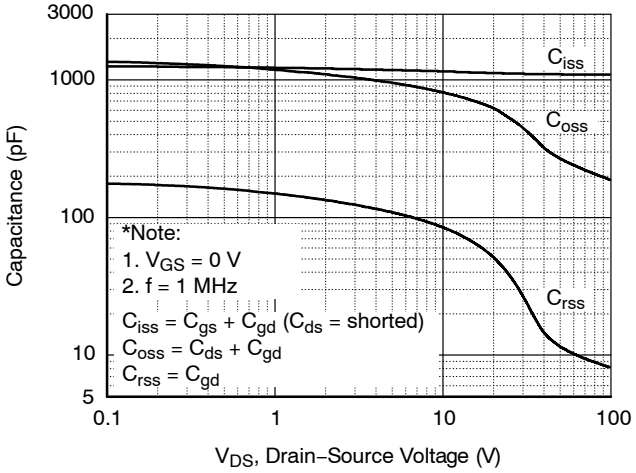


Figure 5. Capacitance Characteristics

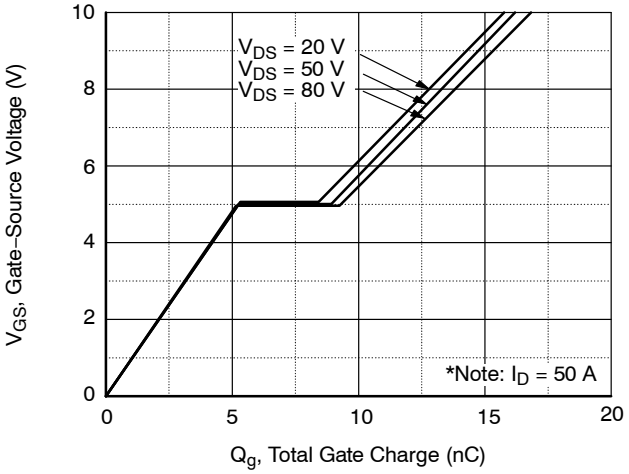


Figure 6. Gate Charge Characteristics

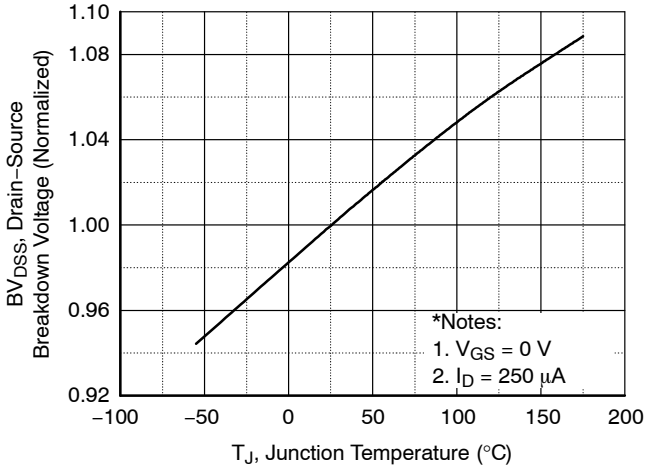


Figure 7. Breakdown Voltage Variation vs. Temperature

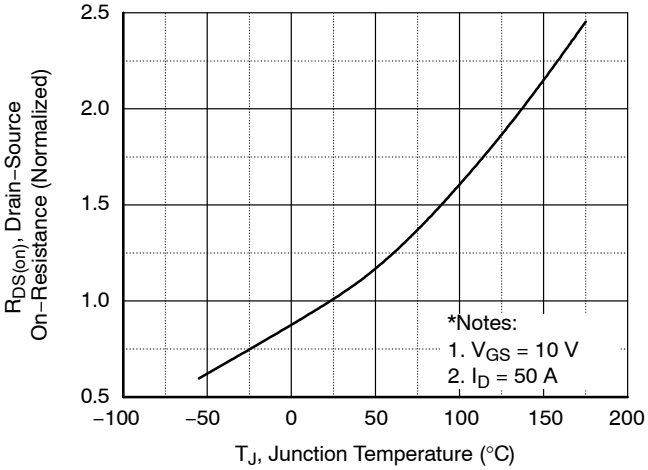


Figure 8. On−Resistance Variation vs. Temperature

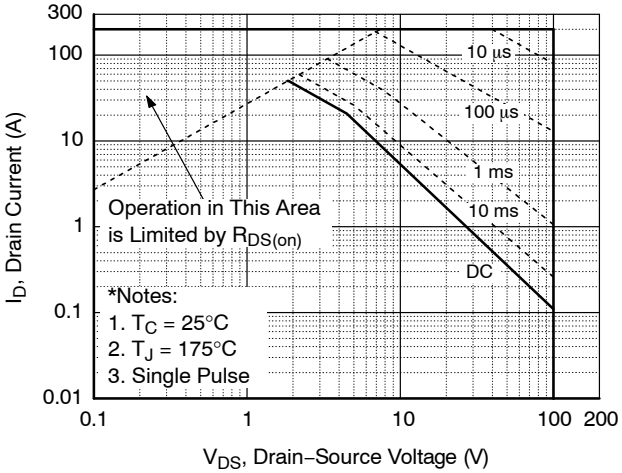


Figure 9. Maximum Safe Operating Area

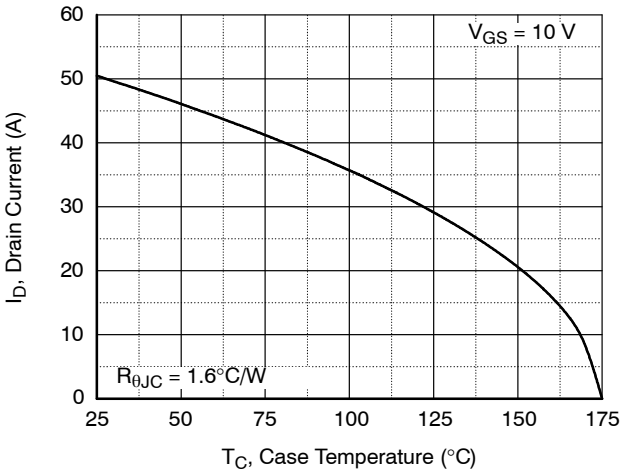


Figure 10. Maximum Drain Current vs. Case Temperature

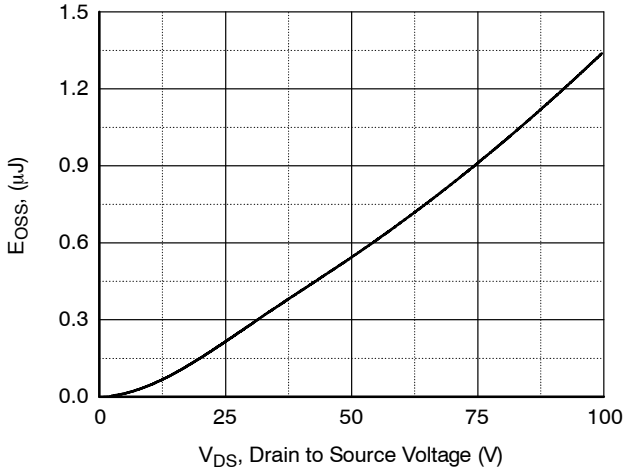


Figure 11. Eoss vs. Drain to Source Voltage

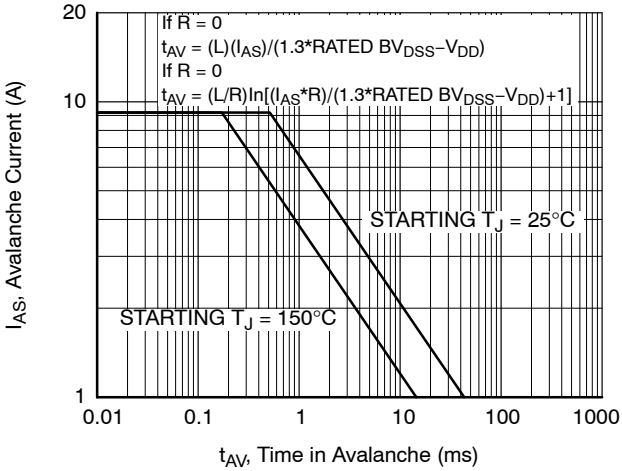


Figure 12. Unclamped Inductive Switching Capability

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

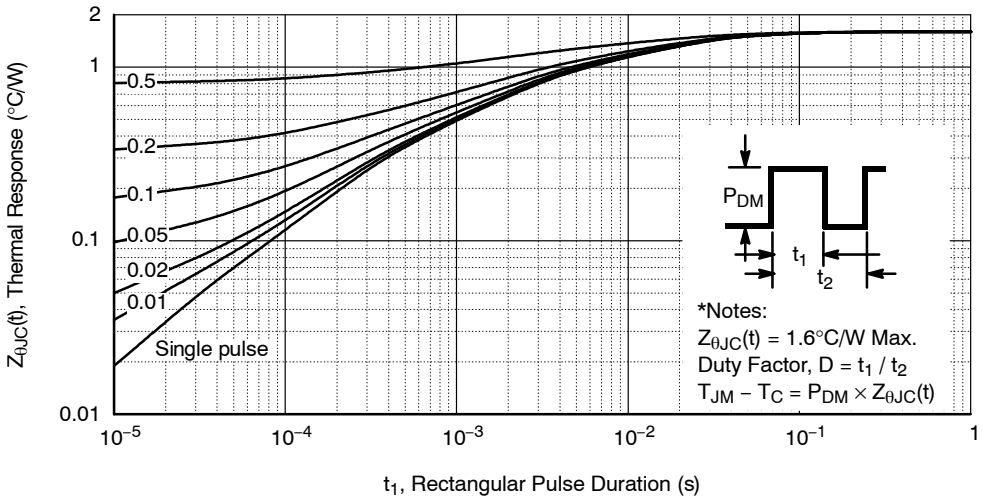


Figure 13. Transient Thermal Response Curve

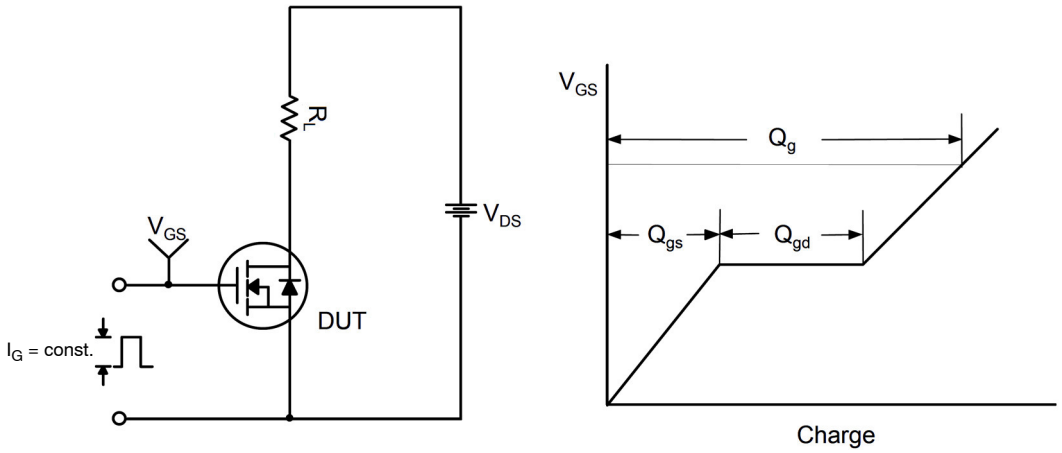


Figure 14. Gate Charge Test Circuit & Waveform

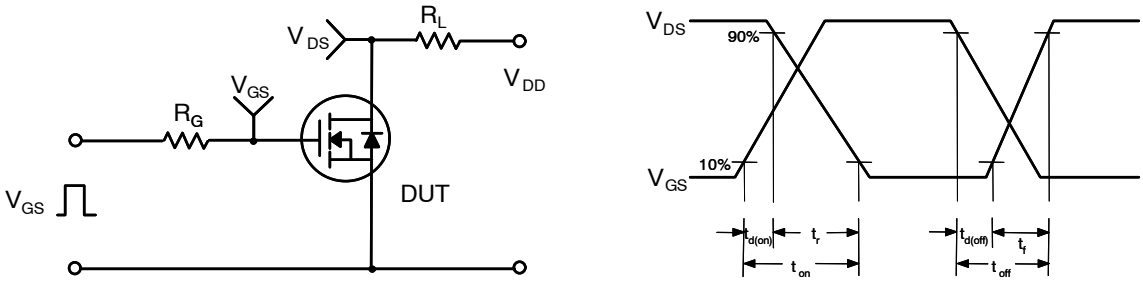


Figure 15. Resistive Switching Test Circuit & Waveforms

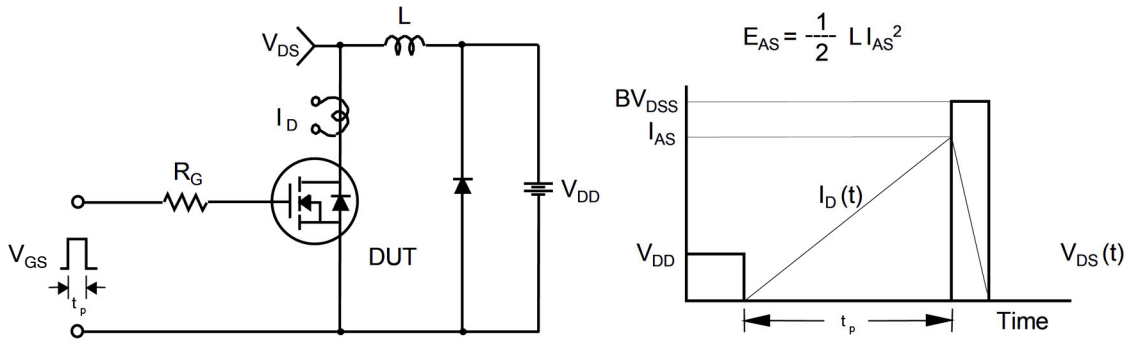


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

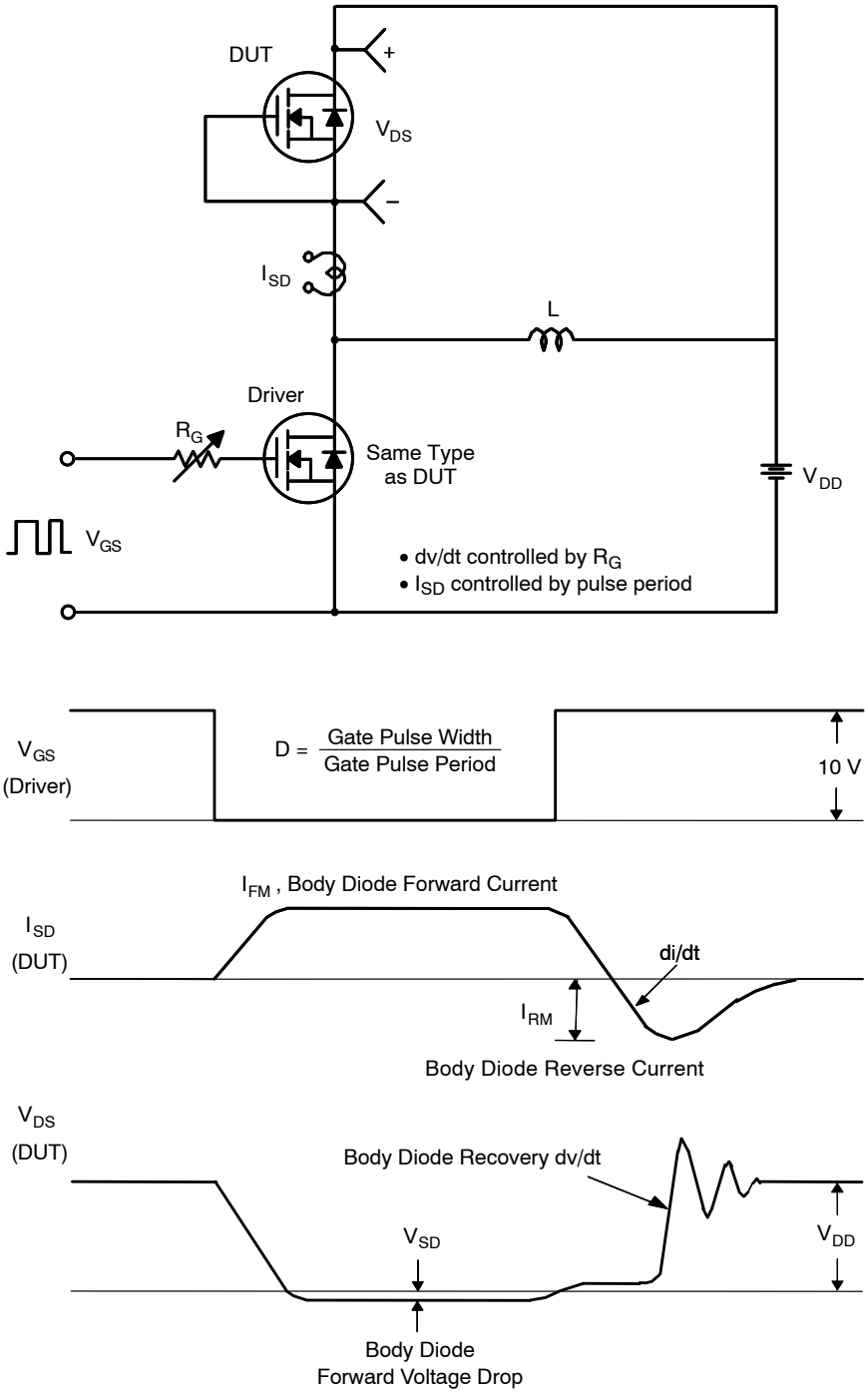
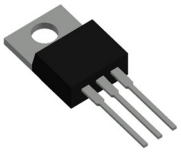


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

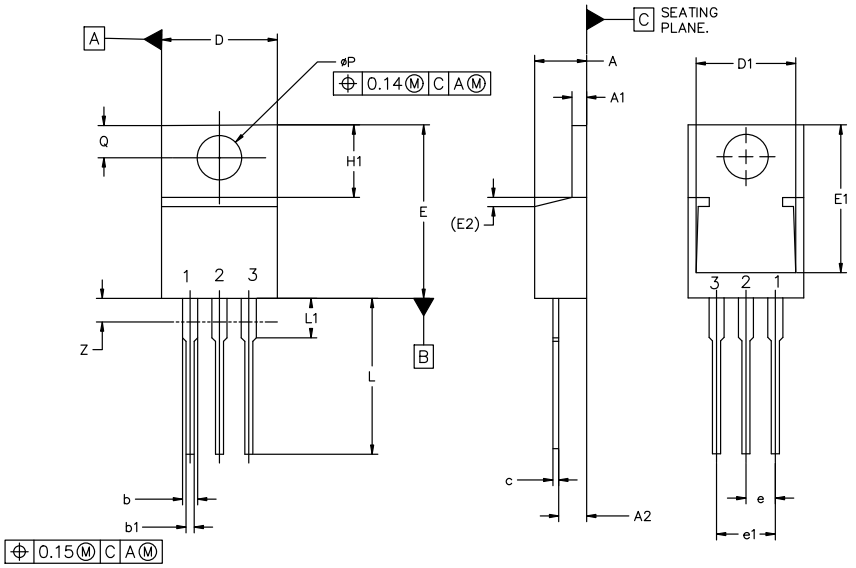
ORDERING INFORMATION

Part Number	Device Marking	Package	Reel Size	Tape Width	Shipping
FDP150N10A–F102	FDP150N10A	TO–220	N/A	N/A	800 Units / Tube



TO−220−3 10.10x15.12x4.45, 2.54P
CASE 221A
ISSUE AL

DATE 05 FEB 2025



MILLIMETERS			
DIM	MIN	NOM	MAX
A	4.07	4.45	4.83
A1	1.15	1.28	1.41
A2	2.04	2.42	2.79
b	1.15	1.34	1.52
b1	0.64	0.80	0.96
c	0.36	0.49	0.61
D	9.66	10.10	10.53
D1	8.43	8.63	8.83
E	14.48	15.12	15.75
E1	12.58	12.78	12.98
E2	1.27 REF		

MILLIMETERS			
DIM	MIN	NOM	MAX
e	2.42	2.54	2.66
e1	4.83	5.08	5.33
H1	5.97	6.22	6.47
L	12.70	13.49	14.27
L1	2.80	3.45	4.10
Q	2.54	2.79	3.04
øP	3.60	3.85	4.09
Z	−.−−	−.−−	3.48

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
4. EMITTER

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

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DESCRIPTION:	**TO−220−3 10.10x15.12x4.45, 2.54P**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales